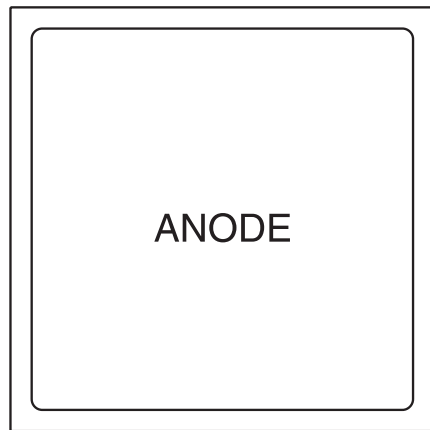


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	52 X 52 MILS
Die Thickness	9 MILS
Anode Bonding Pad Area	47 X 47 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 10,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

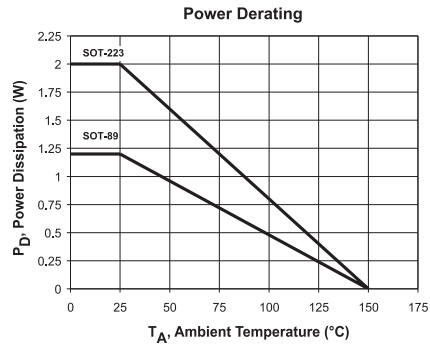
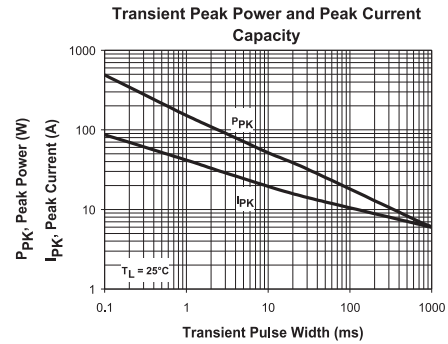
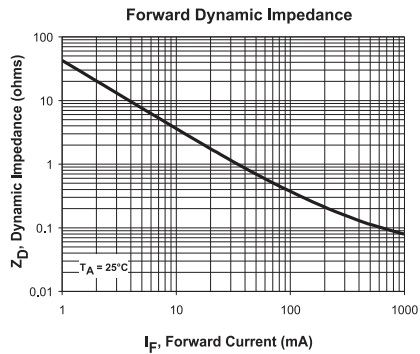
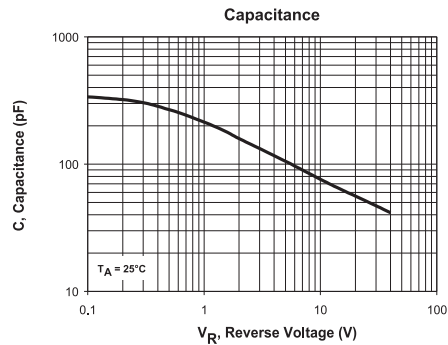
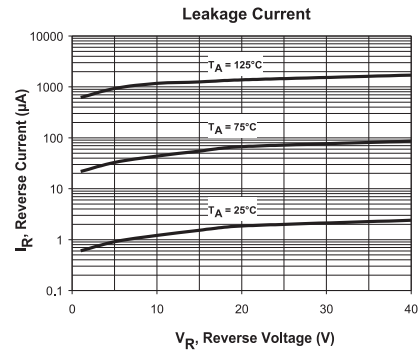
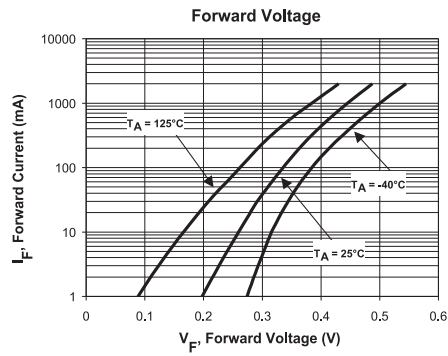
5,110

PRINCIPAL DEVICE TYPES

1N5817
1N5818
1N5819
CXSH-4
CZSH-4

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